

Spectral reflectometry characterization of an extreme ultraviolet attenuated phase-shifting mask blank (Erratum)

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This article [*J. Micro/Nanopattern. Mater. Metrol.*, **23**(4), 041402 (2024) <https://doi.org/10.1117/1.JMM.23.4.041402>] was originally published online on 12 July 2024 with errors in Table 1 and in the Materials and Methods section. STEM measurements in the table and their corresponding mentions in the text were incorrect. The original table is shown below:

Table 1 Sample layer thickness summary.

Layer	Design (nm)	STEM (nm)	REGINE (nm)
Absorber	33	37.53 ± 0.25	37.7(6)
Ru	2.5	2.48 ± 0.37	2.1(2)
Ru ₂ Si ₃	N/A	1.53 ± 0.38	1.5(1)
Si	4.2	1.86 ± 0.04	N/A
MoSi ₂	N/A	1.69 ± 0.04	N/A
Mo	2.8	1.94 ± 0.04	N/A
MoSi ₂	N/A	1.80 ± 0.04	N/A

The corrected table appears below:

Table 1 Sample layer thickness summary.

Layer	Design (nm)	STEM (nm)	REGINE (nm)
Absorber	33	37.53 ± 0.25	37.7(6)
Ru	2.5	2.48 ± 0.37	2.1(2)
Ru ₂ Si ₃	N/A	1.53 ± 0.38	1.5(1)
Si	4.2	1.86 ± 0.30	N/A
MoSi ₂	N/A	1.69 ± 0.30	N/A
Mo	2.8	1.94 ± 0.28	N/A
MoSi ₂	N/A	1.80 ± 0.29	N/A

The affected portion of the text in Sec. 2.1 has been corrected to read:

“We estimated the thicknesses of Si, Mo, MoSi₂ (grown on top of Si), MoSi₂ (grown on top of Mo) as 1.86 ± 0.30 , 1.94 ± 0.28 , 1.80 ± 0.29 , and 1.69 ± 0.30 nm, respectively.”

The article was corrected on 25 July 2024.